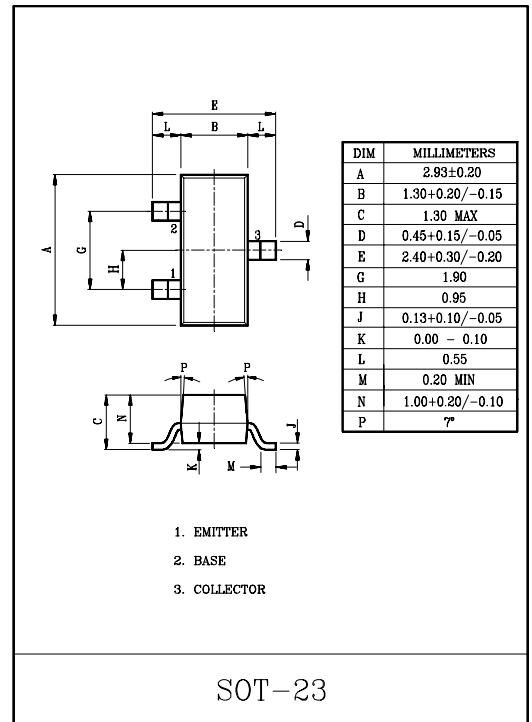
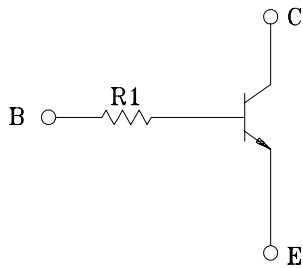


SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	100	mA

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

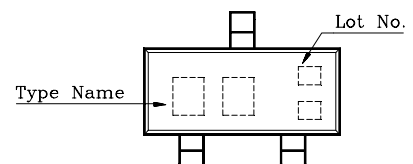
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I _{CBO}	V _{CB} =50V, I _E =0	-	-	100	nA	
Emitter Cut-off Current	I _{EBO}	V _{EB} =5V, I _C =0	-	-	100	nA	
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =1mA	120	-	-		
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =10mA, I _B =0.5mA	-	0.1	0.3	V	
Transition Frequency	f _T *	V _{CE} =10V, I _C =5mA	-	250	-	MHz	
Input Resistor	KRC110S	R ₁		-	4.7	-	kΩ
	KRC111S			-	10	-	
	KRC112S			-	100	-	
	KRC113S			-	22	-	
	KRC114S			-	47	-	

Note : * Characteristic of Transistor Only

MARK SPEC

TYPE	KRC110S	KRC111S	KRC112S	KRC113S	KRC114S
MARK	NK	NM	NN	NO	NP

Marking



KRC110S ~ KRC114S

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Switching Time	Rise Time	KRC110S	V _O =5V V _{IN} =5V R _L =1kΩ	-	0.025	-	μS	
		KRC111S		-	0.03	-		
		KRC112S		-	0.3	-		
		KRC113S		-	0.06	-		
		KRC114S		-	0.11	-		
	Storage Time	KRC110S		t _{stg}	-	3.0		-
		KRC111S		-	-	2.0		-
		KRC112S		-	-	6.0		-
		KRC113S		-	-	4.0		-
		KRC114S		-	-	5.0		-
	Fall Time	KRC110S		t _f	-	0.2		-
		KRC111S		-	-	0.12		-
		KRC112S		-	-	2.0		-
		KRC113S		-	-	0.9		-
		KRC114S		-	-	1.4		-